ABSTRACT

The present invention is provided to form a metal line layer in a semiconductor device, wherein at least one conductive layer of a plurality of conductive layers is etched, a side wall oxide film is formed on side walls of some conductive layers of the etched conductive layers, and then the other conductive layers are etched. According to the present invention, since it is possible to prevent attacks against the side walls, which may occur due to sputtering and bending of plasma ions, it is possible to enhance yield and reliability of a semiconductor device.